

UTC8550S PNP EPITAXIAL SILICON TRANSISTOR

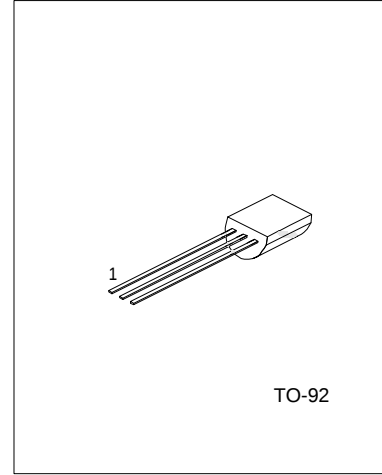
LOW VOLTAGE HIGH CURRENT SMALL SIGNAL PNP TRANSISTOR

FEATURES

- *Collector current up to 800mA
- *Collector-Emitter voltage up to 20 V
- *Complimentary to 8050S

APPLICATIONS

- *Class B push-pull audio amplifier
- *General purpose applications



1:EMITTER 2: COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETERS	SYMBOL	RATING	UNITS
Collector-base voltage	V _{CB0}	-30	V
Collector-emitter voltage	V _{CEO}	-20	V
Emitter-base voltage	V _{EB0}	-5	V
Collector dissipation(Ta=25°C)	P _c	1	W
Collector current	I _c	-800	mA
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-65 ~ +150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV _{CB0}	I _c =-100μA, I _E =0	-30			V
Collector-emitter breakdown voltage	BV _{CEO}	I _c =-1mA, I _B =0	-20			V
Emitter-base breakdown voltage	BV _{EB0}	I _E =-100μA, I _c =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-30V, I _E =0			-1	μA
Emitter cut-off current	I _{EB0}	V _{EB} =-5V, I _c =0			-100	nA
DC current gain(note)	h _{FE}	V _{CE} =-1V, I _c =-1mA V _{CE} =-1V, I _c =-150 mA V _{CE} =-1V, I _c =-500mA	100 120 40	110	400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-500mA, I _B =-50mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =500mA, I _B =-50mA			-1.2	V
Base-emitter saturation voltage	V _{BE}	V _{CE} =-1V, I _c =-10mA			-1.0	V
Current gain bandwidth product	f _T	V _{CE} =-10V, I _c =-50mA	100			MHz
Output capacitance	C _{ob}	V _{CB} =10V, I _E =0 f=1MHz		9.0		pF

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CLASSIFICATION OF hFE2

RANK	C	D	E
RANGE	120-200	160-300	280-500

TYPICAL CHARACTERISTIC CURVES

